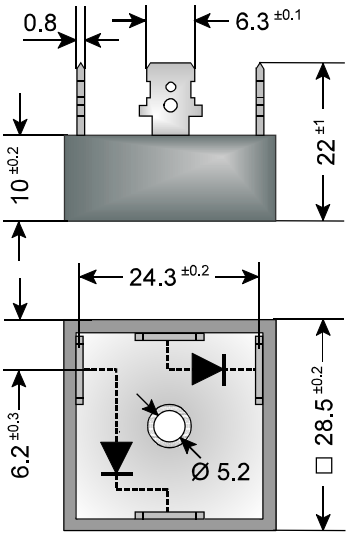
Silicon-Twin Rectifiers **Silizium-Doppeldioden**



Dimensions / Maße in mm

Nominal current Nennstrom	60 A
Alternating input voltage Eingangswechselspannung	60…800 V
Plastic case with alu-bottom Kunststoffgehäuse mit Alu-Boden	
Dimensions Abmessungen	28.5 x 28.5 x 10 [mm]
Weight approx. Gewicht ca.	23 g
Compound has classification UL94V-0 Vergußmasse UL94V-0 klassifiziert	
Standard packaging: bulk Standard Lieferform: lose im Karton	see page 22 s. Seite 22

Recognized Product – Underwriters Laboratories Inc.® File E175067
Anerkanntes Produkt – Underwriters Laboratories Inc.® Nr. E175067

Maximum ratings **Grenzwerte**

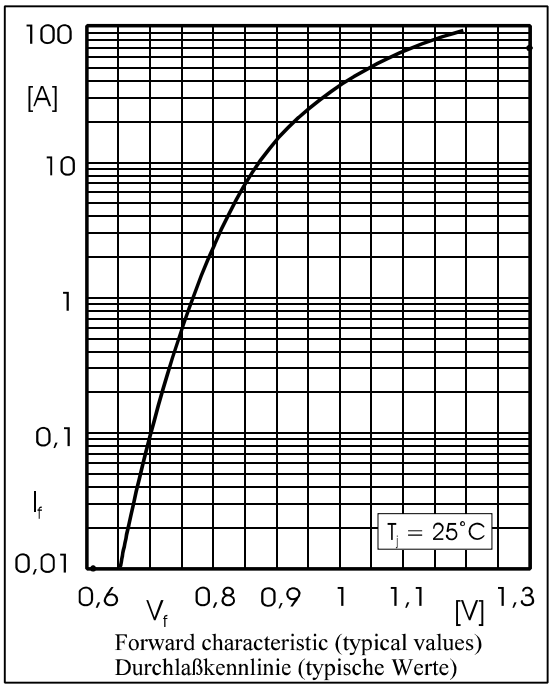
Type Typ	Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] [1])	Surge peak reverse voltage Stoßspitzensperrspannung V_{RRM} [V] [1])
D60 VC20	200	200
D60 VC40	400	400
D60 VC60	600	600
D60 VC80	800	800
D60 VC100	1000	1000
D60 VC120	1200	1200

Repetitive peak forward current Periodischer Spitzenstrom	f > 15 Hz	I_{FRM}	120 A [2])
Peak forward surge current, 50 Hz half sine-wave Stoßstrom für eine 50 Hz Sinus-Halbwelle	T_A = 25˚C	I_{FSM}	450 A
Rating for fusing – Grenzlastintegral, t < 10 ms	T_A = 25˚C	i^2t	1000 A^2s
Isolation voltage – Isolationsspannung	t = 1 min	V_{ISO}	> 2000 V
Operating junction temperature – Sperrschichttemperatur		T_j	– 50…+150˚C
Storage temperature – Lagerungstemperatur		T_S	– 50…+150˚C

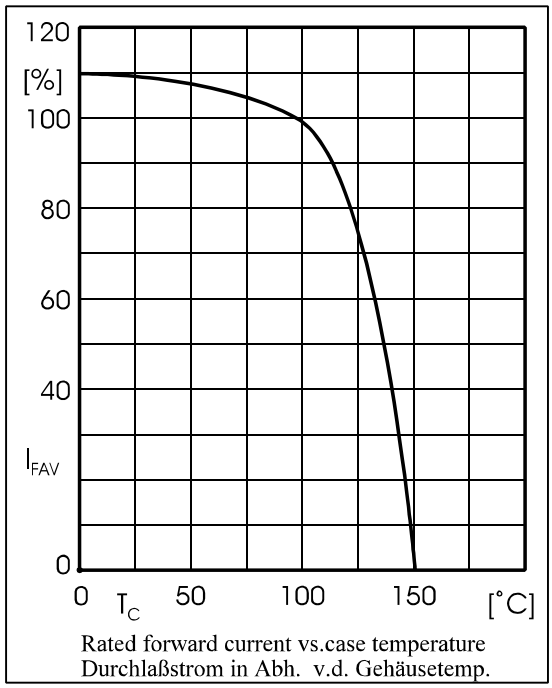
[1]) Valid per diode – Gültig pro Diode
[2]) Max. case temperature T_C = 100˚C – Max. Gehäusetemperatur T_C = 100˚C

Characteristics — Kennwerte

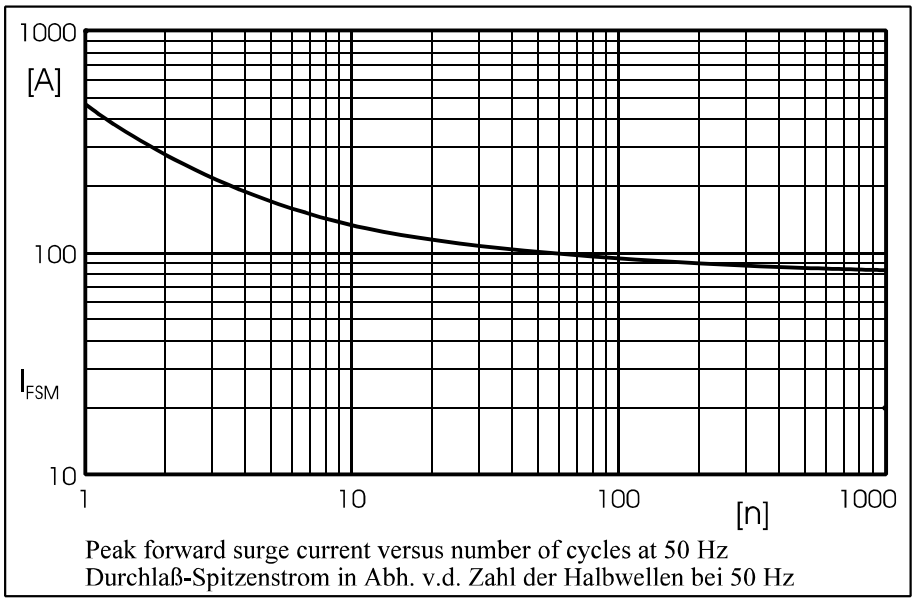
Forward voltage – Durchlaßspannung	$T_j = 25^\circ C$	$I_F = 60$ A	V_F	< 1.1 V [1])
Leakage current – Sperrstrom	$T_j = 25^\circ C$	$V_R = V_{RRM}$	I_R	< 100 µA
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse			R_{thC}	< 0.6 K/W
Admissible torque for mounting Zulässiges Anzugsdrehmoment		10-32 UNF M 5		18 ± 10% lb.in. 2 ± 10% Nm



Forward characteristic (typical values)
Durchlaßkennlinie (typische Werte)



Rated forward current vs.case temperature
Durchlaßstrom in Abh. v.d. Gehäusetemp.



Peak forward surge current versus number of cycles at 50 Hz
Durchlaß-Spitzenstrom in Abh. v.d. Zahl der Halbwellen bei 50 Hz

[1]) Valid per diode – Gültig pro Diode